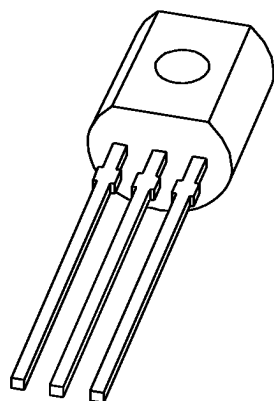


DATA SHEET



BF324

PNP medium frequency transistor

Product specification

1997 Jul 07

Supersedes data of September 1994

File under Discrete Semiconductors, SC04

**Philips
Semiconductors**



PHILIPS

PNP medium frequency transistor

BF324

FEATURES

- Low current (max. 25 mA)
- Low voltage (max. 30 V).

APPLICATIONS

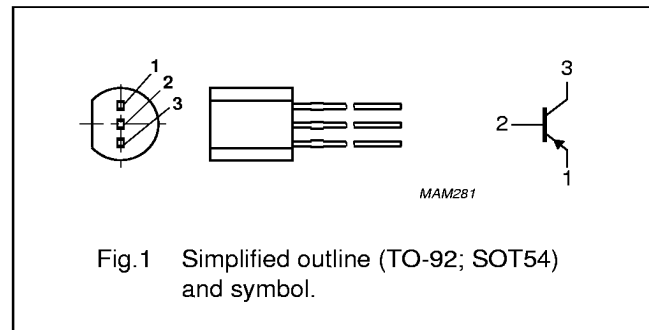
- RF stages in FM front-ends in common base configuration.

DESCRIPTION

PNP medium frequency transistor in a TO-92; SOT54 plastic package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	–30	V
V_{CEO}	collector-emitter voltage	open base	–	–	–30	V
I_{CM}	peak collector current		–	–	–25	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	–	300	mW
h_{FE}	DC current gain	$I_C = -4\text{ mA}; V_{CE} = -10\text{ V}$	25	–	–	
f_T	transition frequency	$I_C = -4\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	–	450	–	MHz

PNP medium frequency transistor

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–30	V
V_{CEO}	collector-emitter voltage	open base	–	–30	V
V_{EBO}	emitter-base voltage	open collector	–	–4	V
I_C	collector current (DC)		–	–25	mA
I_{CM}	peak collector current		–	–25	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$; note 1	–	300	mW
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	420	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -30\text{ V}$	–	–	–50	nA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -4\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}$ $I_C = -1\text{ mA}$ $I_C = -4\text{ mA}$	– 25	45 –	– –	
V_{BE}	base-emitter voltage	$I_C = -4\text{ mA}$; $V_{CE} = -10\text{ V}$	–	760	–	mV
C_{fb}	feedback capacitance	$I_C = 0$; $V_{CE} = -10\text{ V}$; $f = 1\text{ MHz}$	–	–	0.3	pF
f_T	transition frequency	$V_{CE} = -10\text{ V}$; $f = 100\text{ MHz}$ $I_C = -1\text{ mA}$ $I_C = -4\text{ mA}$ $I_C = -8\text{ mA}$	– 400 –	350 450 440	– – –	MHz MHz MHz

PNP medium frequency transistor

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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

